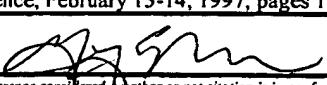


FORM PTO-1449 US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			Atty. Docket No. 80236DPCW Customer No. 01333	Serial No. To Be Assigned		
If AFTER the later date of the first Office Action or 3 months from filing, use only with Rule 97(E) Certificate or Fee			Applicant: Ramanathan Srinivasan, et al			
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			Filing Date Herewith	Group To Be Assigned		
U.S. PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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EXAMINER 			DATE CONSIDERED 9/8/05			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						